

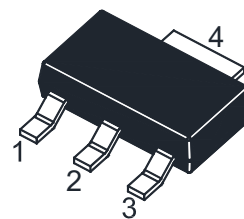
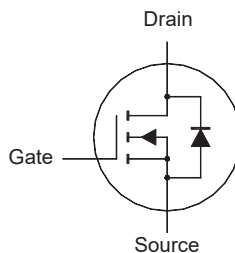
N-Channel Enhancement Mode MOSFET

Features

- Low Gate-Source Threshold Voltage
- Halogen and Antimony Free(HAF),
RoHS compliant

Applications

- LED balance shink switch
- DC/DC aux power
- Synchronus Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial



1.Gate 2.Drain 3.Source 4.Drain
SOT-223 Plastic Package

Key Parameters

Parameter	Value	Unit
BV_{DSS}	100	V
$R_{DS(ON)}$ Max	280 @ $V_{GS} = 10$ V	m Ω
	285 @ $V_{GS} = 4.5$ V	
$V_{GS(th)}$ typ	1.7	V
Q_g typ	8.5 @ $V_{GS} = 10$ V	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	4	A
$T_c = 25^\circ\text{C}$ $T_c = 100^\circ\text{C}$		2.5	
Peak Drain Current, Pulsed ¹⁾	I_{DM}	12	A
Single-Pulse Avalanche Current	I_{AS}	2.1	A
Single-Pulse Avalanche Energy ²⁾	E_{AS}	1.1	mJ
Power Dissipation	P_D	10.7	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	11.6	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	62	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width ≤ 100 μs , Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.5$ mH, $R_g = 25$ Ω , $I_{AS} = 2.1$ A, $V_{GS} = 10$ V.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 10\text{ mA}$	BV_{DSS}	100	-	-	V
Drain-Source Leakage Current at $V_{DS} = 80\text{ V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 20\text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	$V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance at $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$ at $V_{GS} = 4.5\text{ V}$, $I_D = 2\text{ A}$	$R_{DS(on)}$	- -	250 -	280 285	$\text{m}\Omega$
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 5\text{ V}$, $I_D = 2\text{ A}$	g_{FS}	-	4.4	-	S
Gate Resistance at $V_{DS} = 0\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	R_g	-	1.2	-	Ω
Input Capacitance at $V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	C_{iss}	-	465	-	pF
Output Capacitance at $V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	C_{oss}	-	17	-	pF
Reverse Transfer Capacitance at $V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	C_{rss}	-	13	-	pF
Gate Charge Total at $V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$ at $V_{DS} = 50\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 3\text{ A}$	Q_g	- -	8.5 4	- -	nC
Gate to Source Charge at $V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$	Q_{gs}	-	1.8	-	nC
Gate to Drain Charge at $V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$	Q_{gd}	-	1	-	nC
Turn-On Delay Time at $V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_g = 3.3\text{ }\Omega$	$t_{d(on)}$	-	9	-	ns
Turn-On Rise Time at $V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_g = 3.3\text{ }\Omega$	t_r	-	3	-	ns
Turn-Off Delay Time at $V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_g = 3.3\text{ }\Omega$	$t_{d(off)}$	-	8	-	ns
Turn-Off Fall Time at $V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 3\text{ A}$, $R_g = 3.3\text{ }\Omega$	t_f	-	8	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_S = 1\text{ A}$, $V_{GS} = 0\text{ V}$	V_{SD}	-	-	1.2	V
Body-Diode Continuous Current	I_S	-	-	4	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	12	A
Body Diode Reverse Recovery Time at $I_S = 3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	t_{rr}	-	16.5	-	ns
Body Diode Reverse Recovery Charge at $I_S = 3\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	Q_{rr}	-	14.5	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

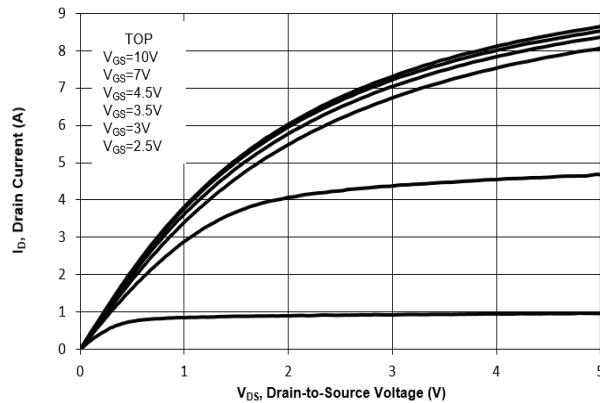


Fig. 2 Typical Transfer Characteristics

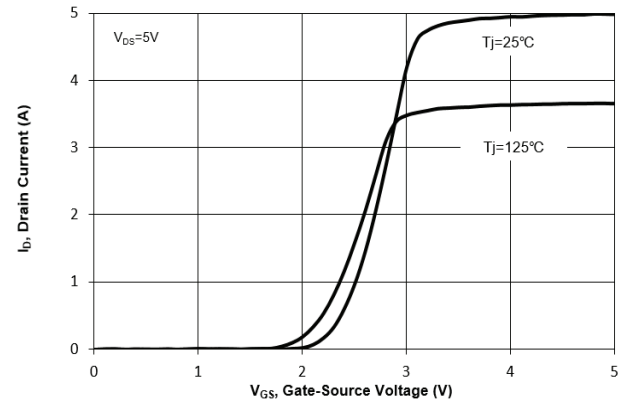


Fig. 3 On-Resistance vs. Drain Current

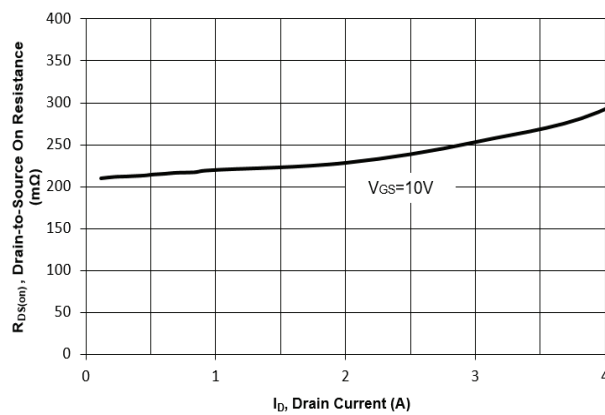


Fig. 4 On-Resistance vs. Gate to Source Voltage

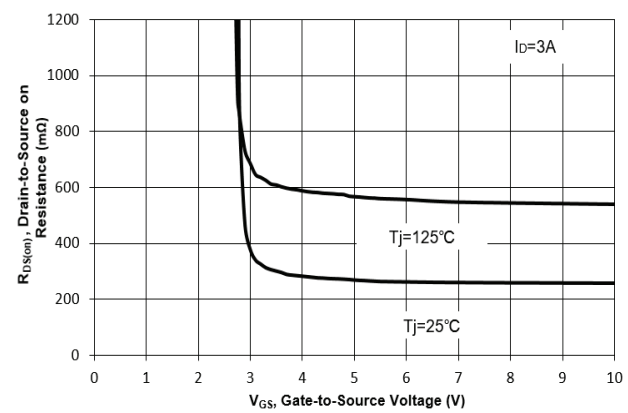


Fig. 5 On-Resistance vs. T_J

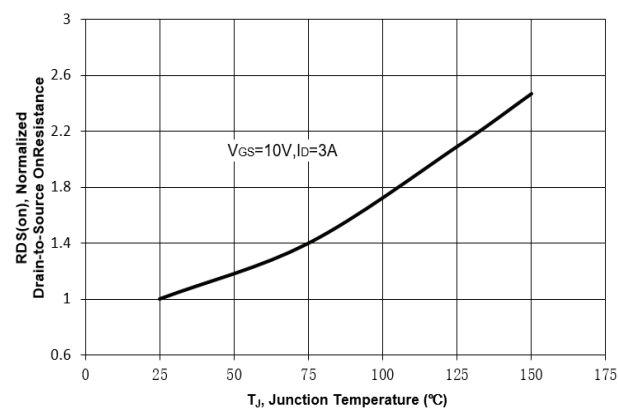
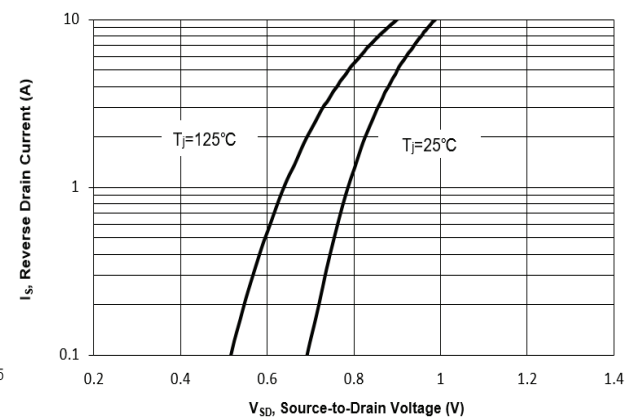


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

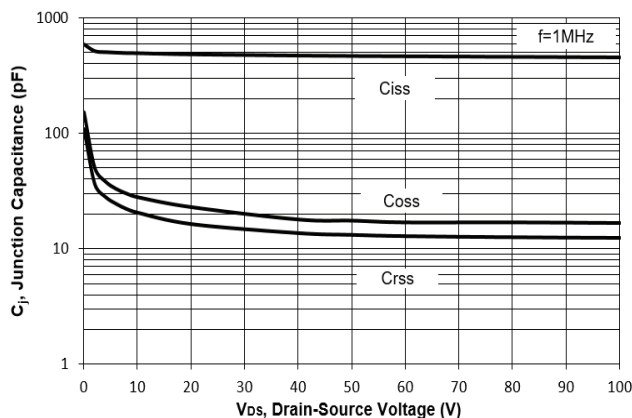


Fig. 8 Drain-Source Leakage Current vs. T_J

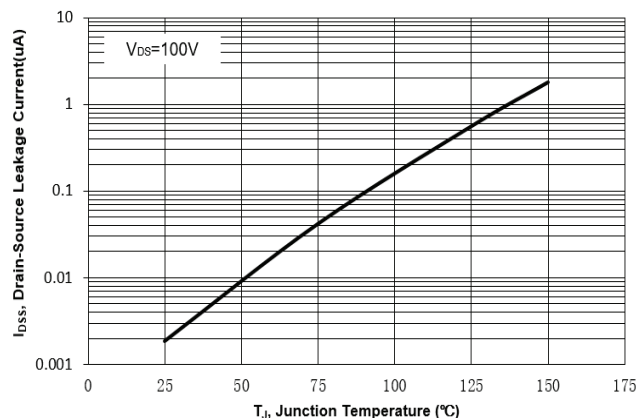


Fig. 9 V_{(BR)DSS} vs. Junction Temperature

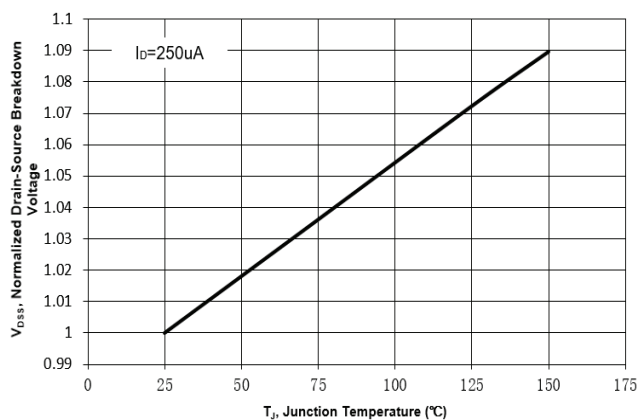


Fig. 10 Gate Threshold Variation vs. T_J

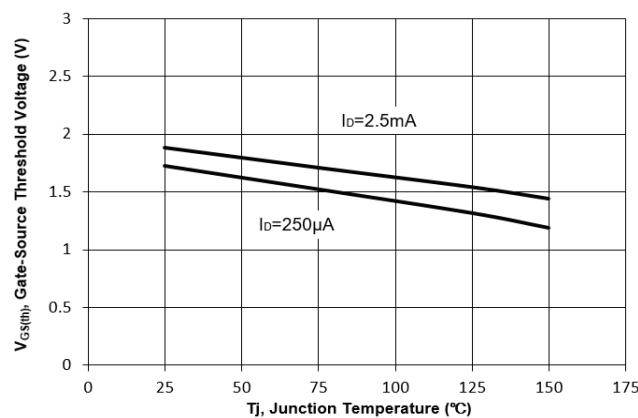


Fig. 11 Gate Charge

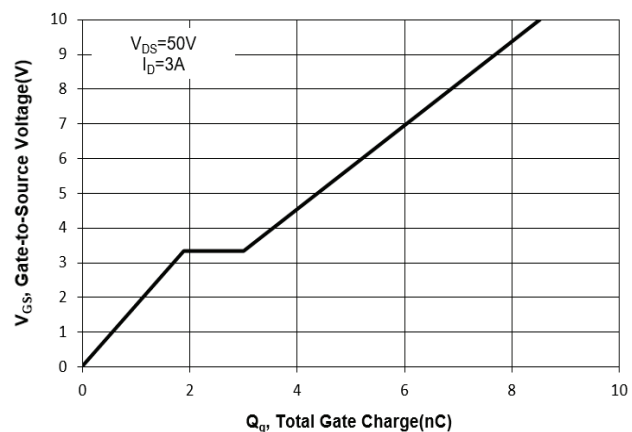
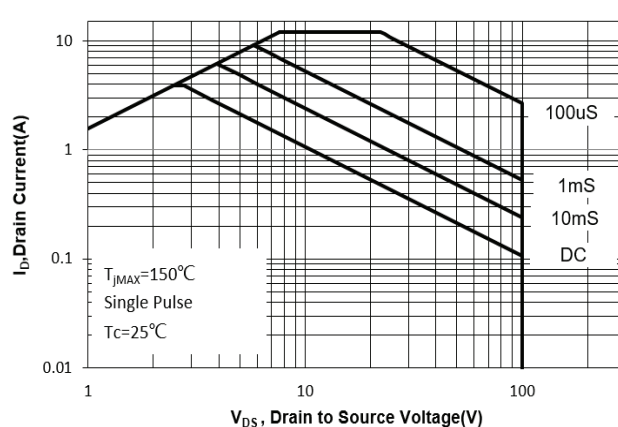
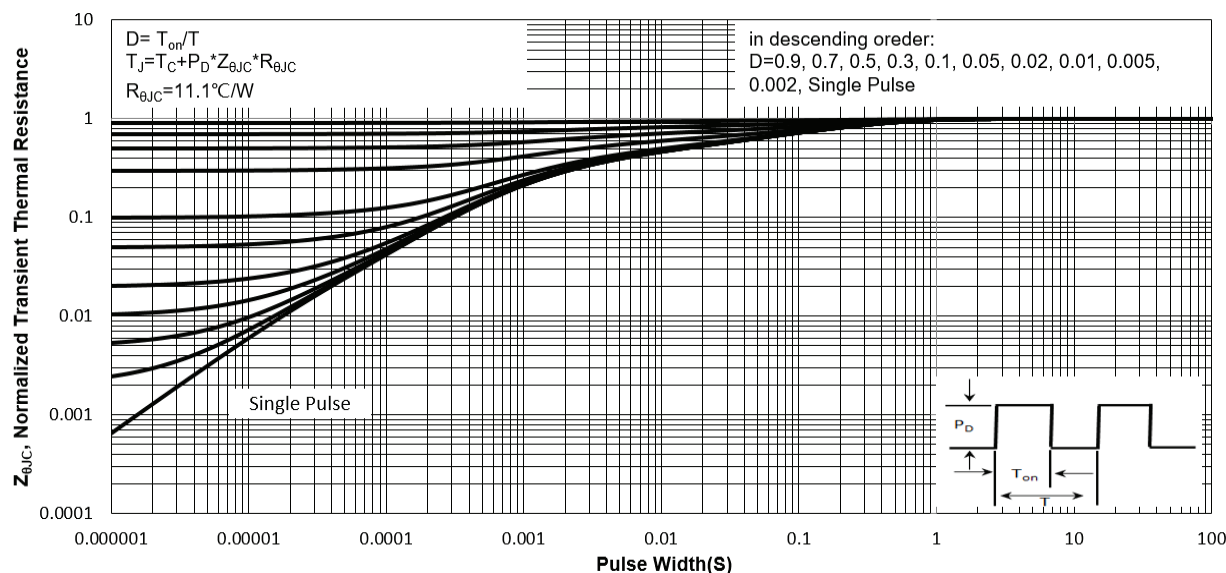
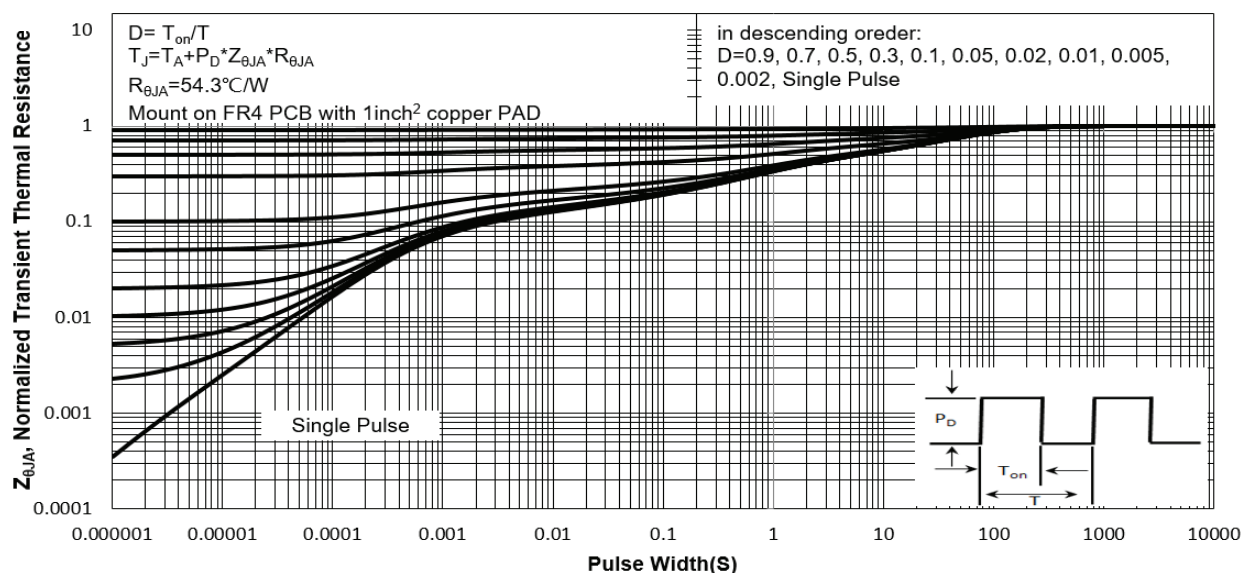


Fig. 12 Safe Operation Area



Electrical Characteristics Curves
Fig. 13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)

Fig. 14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)


Test Circuits

Fig.1-1 Switching times test circuit

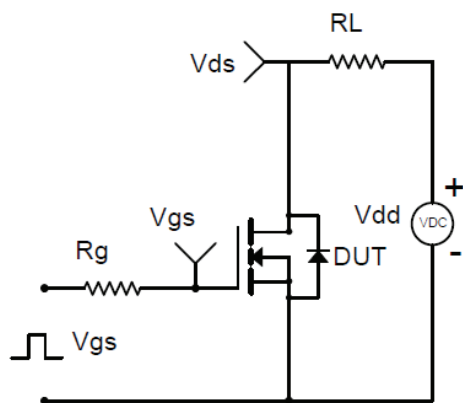


Fig.1-2 Switching Waveform

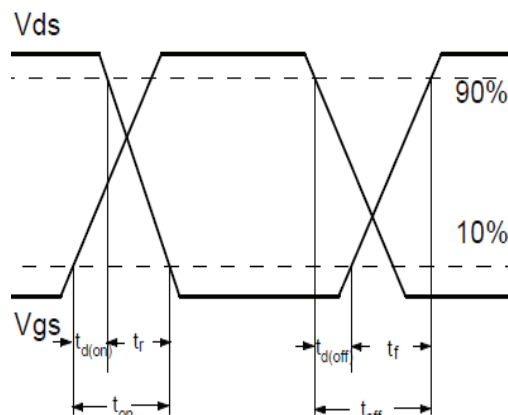


Fig.2-1 Gate charge test circuit

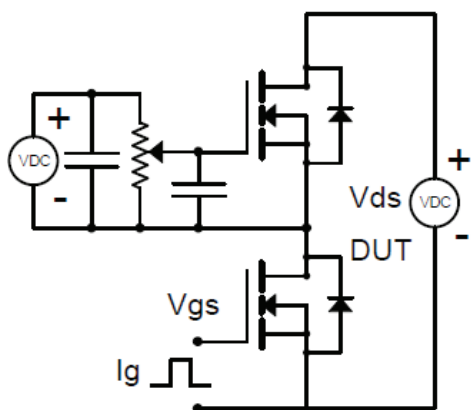


Fig.2-2 Gate charge waveform

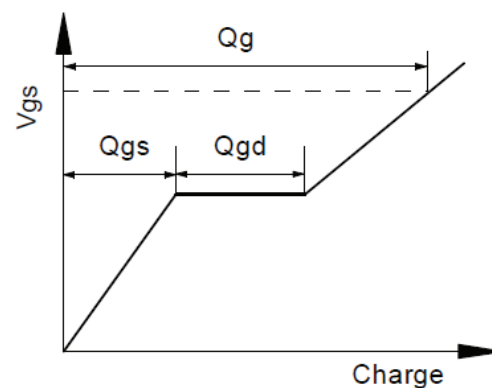


Fig.3-1 Avalanche test circuit

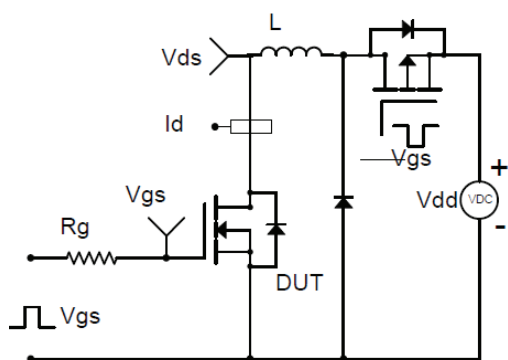
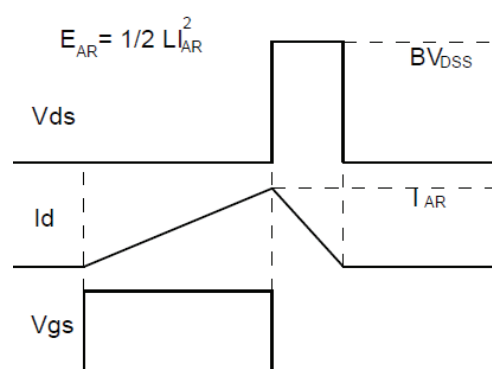
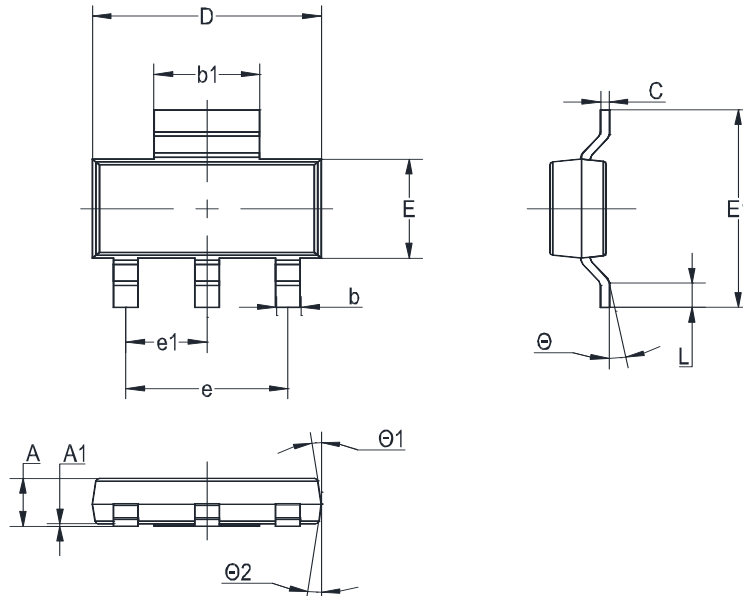
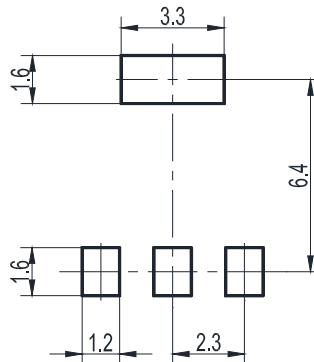


Fig.3-2 Avalanche waveform



Package Outline (Dimensions in mm)
SOT-223


Unit	A	A1	b	b1	C	D	E	E1	e	e1	L	Θ	Θ1	Θ2
mm	1.8 1.5	0.1 MAX	0.8 0.6	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	7.3 6.7	4.6 TYP	2.3 TYP	1.1 0.7	10° 0°	7° 0°	7° 0°

Recommended Soldering Footprint

Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-223	12	8 ± 0.1	0.315 ± 0.004	330	13	3,000

Marking information

" TQ10N2K6LS " = Part No.

" ***** " = Date Code Marking

Font type: Arial



Disclaimer: Our company reserve the right to make modifications, enhancements, improvements, corrections or other changes to improve product design, functions and reliability, anytime without notice.